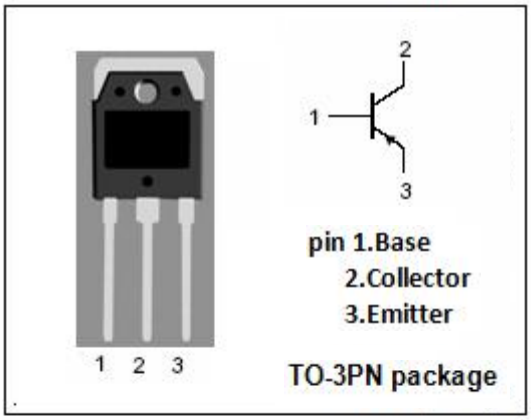
isc Silicon PNP Power Transistor — MJE4353

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= -160V(Min)
- DC current gain -
  : h_{FE} = 15 (Min) @I_C= -8 A
  : h_{FE} = 8 (Min) @I_C= -16A
- Complement to Type MJE4343
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

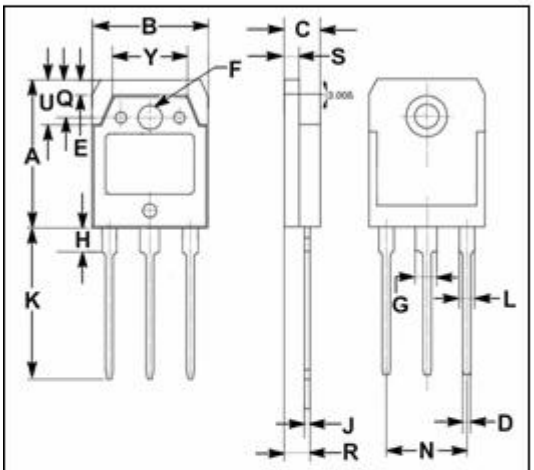
- For use in high power audio amplifier and switching regulator circuits

ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-160	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current -Continuous	-16	A
I_B	Base Current	-5	A
P_C	Collector Power Dissipation @T_C=25℃	125	W
T_j	Junction Temperature	-65~150	℃
T_{stg}	Storage Temperature	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.0	℃/W



DIM	mm MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

isc Silicon PNP Power Transistor MJE4343

ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -100mA ;I_B= 0	-160		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= -8A ;I_B= -0.8A		-2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= -16A ;I_B= -2A		-3.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -16A ;I_B= -2A		-3.9	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -16A ; V_{CE}= -4V		-3.9	V
I_{CBO}	Collector-Base Cutoff Current	V_{CB}= -160V; I_E= 0		-750	μA
I_{CEO}	Collector-Emitter Cutoff Current	V_{CB}= -80V; I_E= 0		-750	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -7V; I_C= 0		-1	mA
h_{FE-1}	DC Current Gain	I_C= -8A ; V_{CE}= -2V	15		
h_{FE-2}	DC Current Gain	I_C= -16A ; V_{CE}= -4V	8		